TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2 S D 1 4 1 1 A

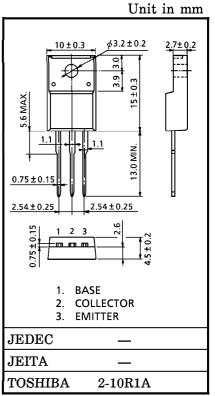
HIGH CURRENT SWITCHING APPLICATIONS

POWER AMPLIFIER APPLICATIONS

- Low Saturation Voltage : $V_{CE (sat)} = 0.5V$ (Max.) at $I_{C} = 4A$
- Complementary to 2SB1018A

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Collector-Base Voltage	v_{CBO}	100	V	
Collector-Emitter Voltage	v_{CEO}	80	V	
Emitter-Base Voltage	$V_{ m EBO}$	5	V	
Collector Current	$_{ m IC}$	7	A	
Base Current	IB	1	A	
Collector Power Ta=25°C	$P_{\mathbf{C}}$	2.0	\mathbf{w}	
Dissipation Tc=25°C		30] **	
Junction Temperature	$T_{ m j}$	150	°C	
Storage Temperature Range	$ m T_{stg}$	-55~150	°C	

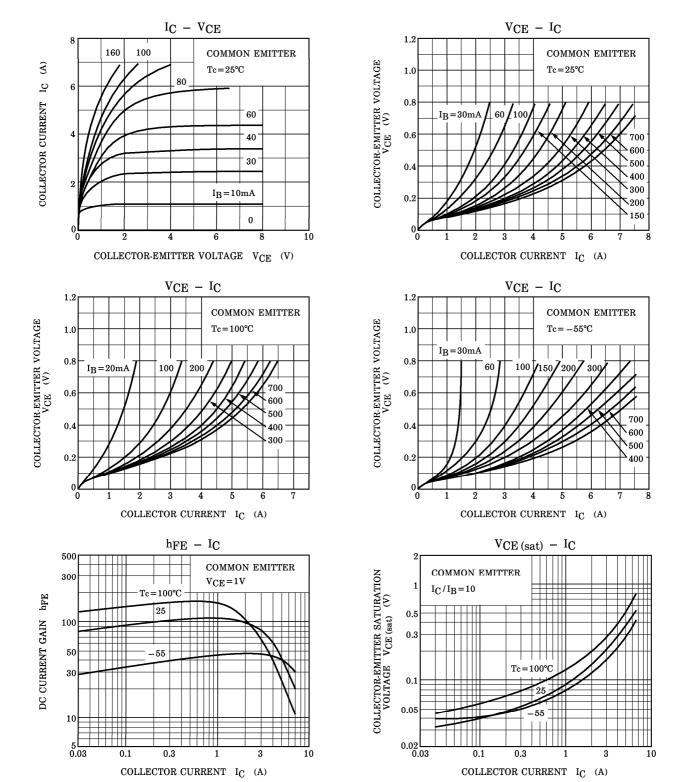


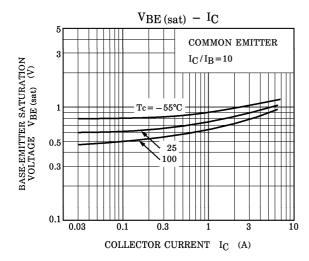
Weight: 1.7 g (Typ.)

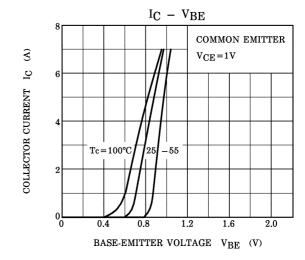
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

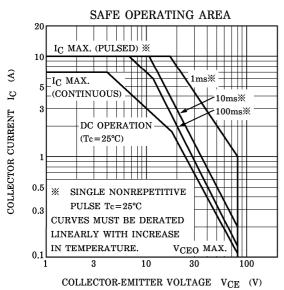
CHARAC	CTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-	off Current	I_{CBO}	$V_{CB} = 100V, I_{E} = 0$	_	_	5	μ A
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_{C}=0$		_	5	μ A
Collector-Emit Voltage	tter Breakdown	V (BR) CEO	$I_{\rm C} = 50 {\rm mA}, \ I_{\rm B} = 0$	80	_	_	V
DC Current Gain		h _{FE (1)} (Note)	$V_{\text{CE}}=1V$, $I_{\text{C}}=1A$	70	_	240	
		h _{FE (2)}	$V_{CE}=1V, I_{C}=4A$	30	_	_	
Collector-Emit Voltage	tter Saturation	V _{CE} (sat)	$I_{C}=4A, I_{B}=0.4A$	_	0.25	0.5	v
Base-Emitter Voltage	Saturation	V _{BE} (sat)	$I_{C}=4A, I_{B}=0.4A$		0.9	1.4	V
Transition Frequency		$ m f_{T}$	$V_{CE}=4V, I_{C}=1A$	_	10	_	MHz
Collector Output Capacitance		C _{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		200	_	pF
Switching Time	Turn-on Time	t _{on}	I_{B1} I_{B2} I_{B2} I_{B2} I_{B2} I_{B2} I_{B2} I_{B2} I_{B2}	l	0.4	_	
	Storage Time	$ m t_{stg}$			2.5	_	$\mu \mathrm{s}$
	Fall Time	t_f	$I_{B1} = -I_{B2} = 0.3A,$ DUTY CYCLE $\leq 1\%$		0.5	_	

(Note) : $h_{FE(1)}$ Classification $O: 70\sim140, Y: 120\sim240$









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